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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	157
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p250-fg256t

Advanced Architecture

The proprietary Automotive ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The Automotive ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM memory
- Extensive CCCs and PLLs
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the Automotive ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

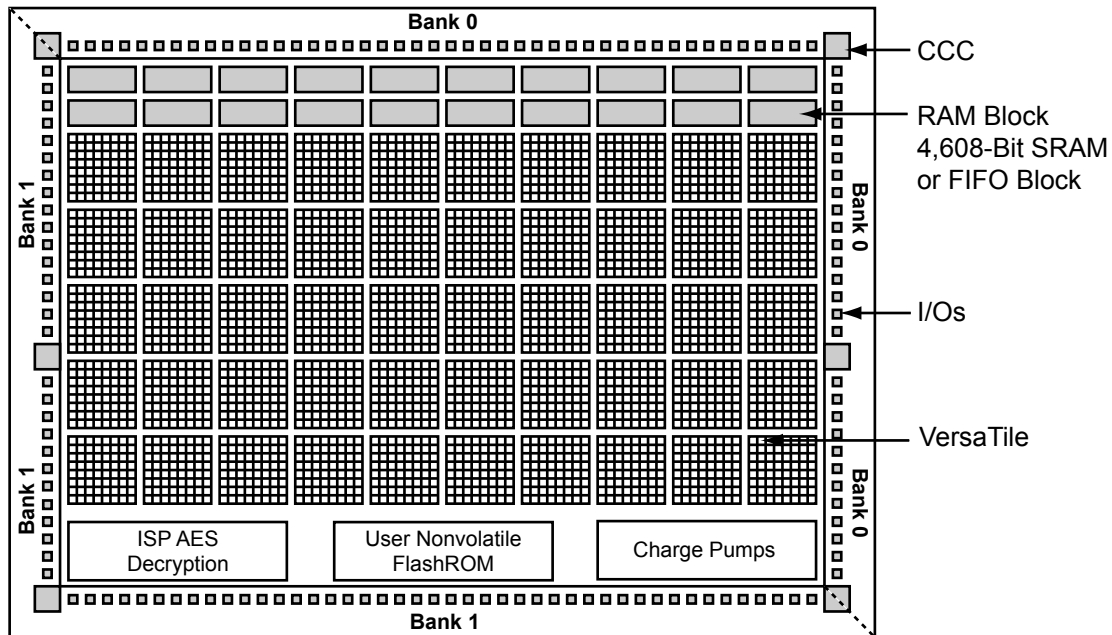


Figure 1-1 • Automotive ProASIC3 Device Architecture Overview with Two I/O Banks (A3P060 and A3P125)

Table 2-3 • Overshoot and Undershoot Limits (as measured on quiet I/Os)

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle	Maximum Overshoot/Undershoot (115°C)	Maximum Overshoot/Undershoot (135°C)
2.7 V or less	10%	0.81 V	0.72 V
	5%	0.90 V	0.82 V
3 V	10%	0.80 V	0.72 V
	5%	0.90 V	0.81 V
3.3 V	10%	0.79 V	0.69 V
	5%	0.88 V	0.79 V
3.6 V	10%	N/A	N/A
	5%	N/A	N/A

Notes:

1. The duration is allowed at one out of six clock cycles (estimated SSO density over cycles). If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
2. This table refers only to overshoot/undershoot limits for simultaneously switching I/Os and does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC[®]3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-2 on page 2-4](#).

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-2 on page 2-4](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.2 V

Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.1 V

Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to V_{CCL}.
- JTAG supply, PLL power supplies, and charge pump V_{PUMP} supply have no influence on I/O behavior.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

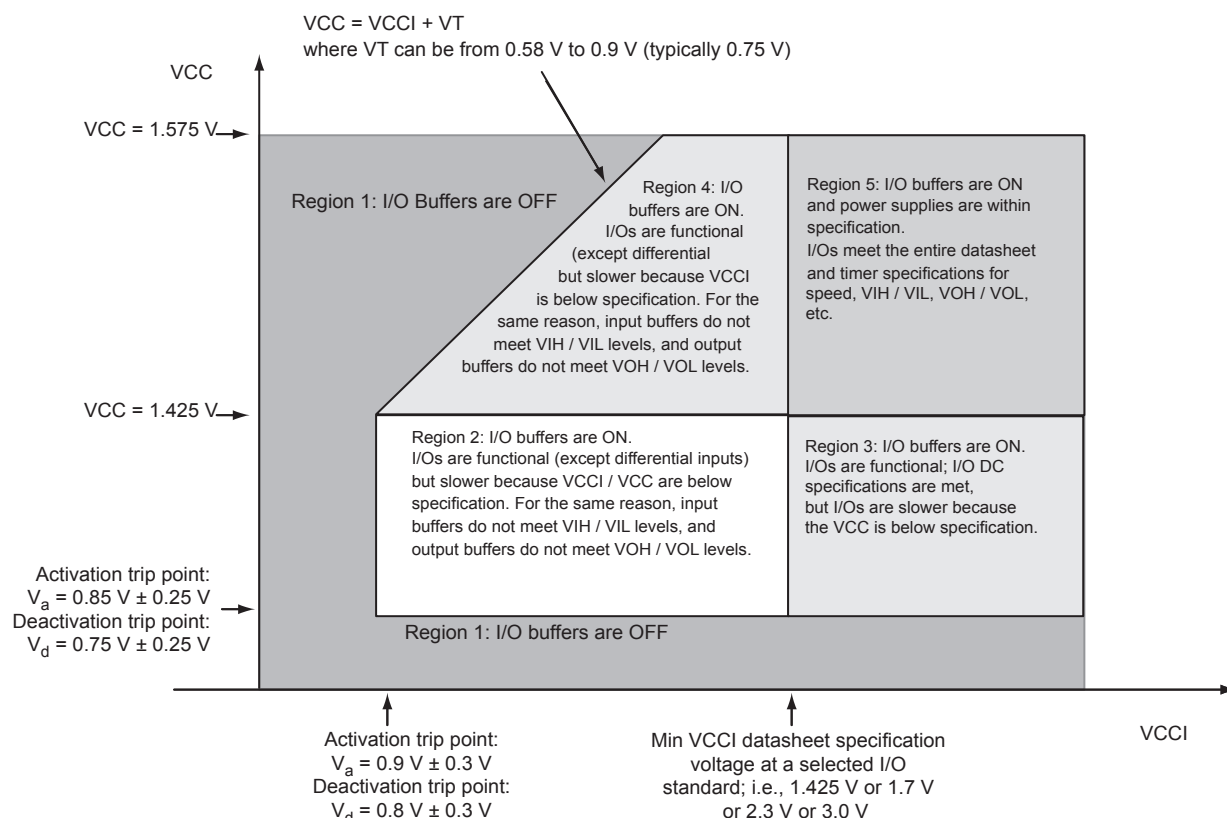


Figure 2-2 • I/O State as a Function of VCCI and VCC Voltage Levels

Thermal Characteristics

Introduction

The temperature variable in Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

EQ 1

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-4 on page 2-5.

P = Power dissipation

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S-CELL} * PAC4) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the [Automotive ProASIC3 FPGA Fabric User's Guide](#).

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the [Automotive ProASIC3 FPGA Fabric User's Guide](#).

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$$

N_{S-CELL} is the number VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

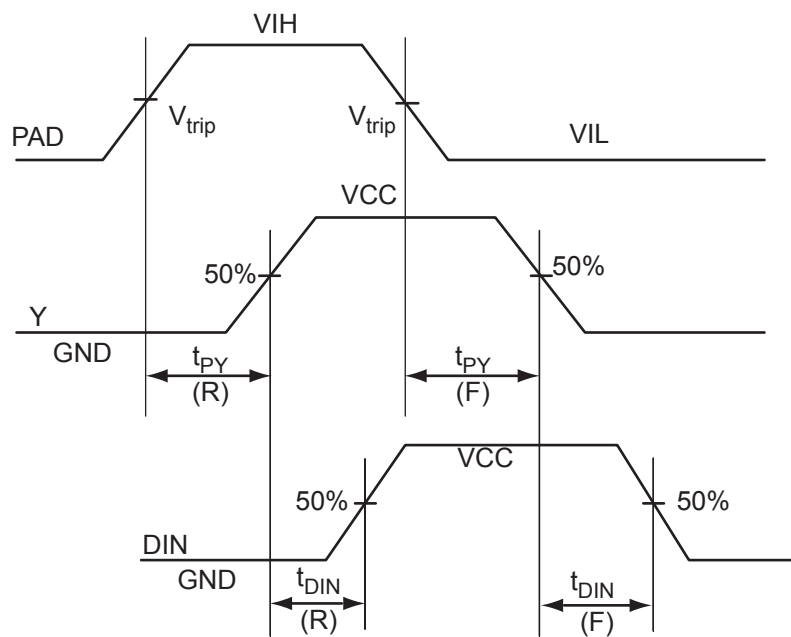
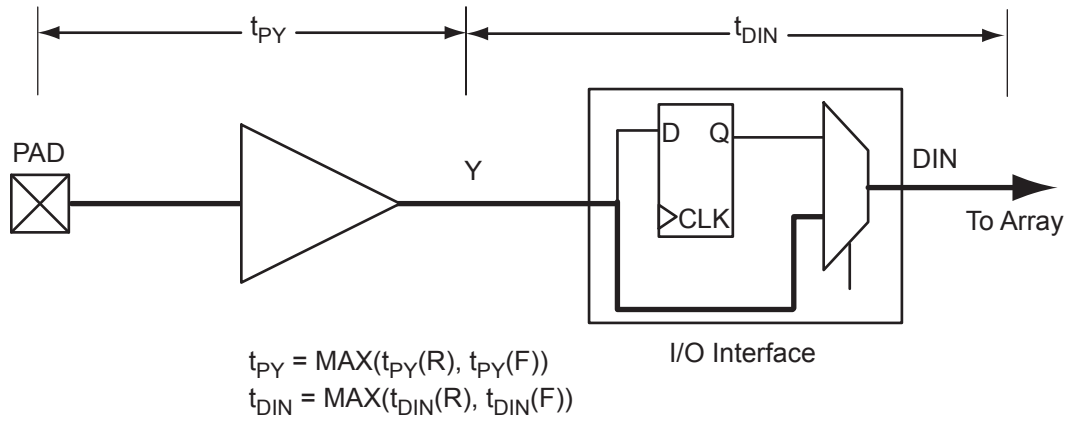


Figure 2-4 • Input Buffer Timing Model and Delays (example)

Table 2-48 • 2.5 V LVC MOS High Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	9.26	0.05	1.45	0.46	8.28	9.26	1.24	1.12	10.78	11.756	ns
	-1	0.55	7.87	0.04	1.23	0.39	7.05	7.87	1.24	1.13	9.17	10	ns
6 mA	STD	0.64	5.43	0.05	1.45	0.46	5.19	5.43	1.43	1.47	7.69	7.926	ns
	-1	0.55	4.62	0.04	1.23	0.39	4.42	4.62	1.43	1.47	6.55	6.743	ns
12 mA	STD	0.64	3.59	0.05	1.45	0.46	3.65	3.51	1.56	1.69	6.15	6.012	ns
	-1	0.55	3.05	0.04	1.23	0.39	3.11	2.99	1.56	1.69	5.23	5.114	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-49 • 2.5 V LVC MOS Low Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	12.12	0.05	1.45	0.46	11.89	12.12	1.25	1.08	14.39	14.622	ns
	-1	0.55	10.31	0.04	1.23	0.39	10.12	10.31	1.25	1.08	12.24	12.438	ns
6 mA	STD	0.64	8.24	0.05	1.45	0.46	8.39	8.23	1.43	1.42	10.89	10.73	ns
	-1	0.55	7.01	0.04	1.23	0.39	7.14	7.00	1.43	1.42	9.26	9.128	ns
12 mA	STD	0.64	6.30	0.05	1.45	0.46	6.41	6.16	1.56	1.63	8.91	8.656	ns
	-1	0.55	5.35	0.04	1.23	0.39	5.45	5.24	1.56	1.63	7.58	7.364	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-70 • 1.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	8.76	0.05	1.59	0.46	7.63	9.35	1.87	1.50	10.13	11.851	ns
	-1	0.55	7.45	0.04	1.35	0.39	6.49	7.95	1.87	1.50	8.62	10.081	ns
4 mA	STD	0.64	5.41	0.05	1.59	0.46	5.42	5.94	2.07	1.84	7.92	8.442	ns
	-1	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.181	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-71 • 1.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	13.51	0.05	1.45	0.46	14.32	14.29	1.88	1.43	16.82	16.794	ns
	-1	0.55	11.49	0.04	1.23	0.39	12.18	12.16	1.88	1.43	14.31	14.286	ns
4 mA	STD	0.64	10.38	0.05	1.45	0.46	11.40	10.67	2.07	1.77	13.90	13.175	ns
	-1	0.55	8.83	0.04	1.23	0.39	9.70	9.08	2.07	1.77	11.82	11.207	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-72 • 1.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	9.05	0.05	1.56	0.45	7.38	9.05	1.81	1.45	9.80	11.47	ns
	-1	0.53	7.70	0.04	1.32	0.38	6.28	7.70	1.81	1.45	8.34	9.75	ns
4 mA	STD	0.63	5.75	0.05	1.56	0.45	5.25	5.75	2.00	1.78	7.67	8.17	ns
	-1	0.53	4.89	0.04	1.32	0.38	4.46	4.89	2.00	1.78	6.52	6.95	ns
6 mA	STD	0.63	5.05	0.05	1.56	0.45	4.92	5.05	2.04	1.87	7.34	7.47	ns
	-1	0.53	4.29	0.04	1.32	0.38	4.19	4.29	2.04	1.87	6.24	6.35	ns
8 mA	STD	0.63	4.41	0.05	1.56	0.45	2.18	1.91	4.27	4.55	3.35	3.11	ns
	-1	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns
12 mA	STD	0.63	4.41	0.05	1.56	0.45	2.18	1.91	4.27	4.55	3.35	3.11	ns
	-1	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-73 • 1.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	13.83	0.05	1.40	0.45	13.86	13.83	1.82	1.39	16.28	16.25	ns
	-1	0.53	11.76	0.04	1.19	0.38	11.79	11.76	1.82	1.39	13.85	13.82	ns
4 mA	STD	0.63	10.83	0.05	1.40	0.45	11.03	10.33	2.00	1.71	13.45	12.75	ns
	-1	0.53	9.21	0.04	1.19	0.38	9.38	8.79	2.01	1.72	11.44	10.84	ns
6 mA	STD	0.63	10.10	0.05	1.40	0.45	10.28	9.62	2.05	1.80	12.70	12.04	ns
	-1	0.53	8.59	0.04	1.19	0.38	8.75	8.18	2.05	1.80	10.81	10.24	ns
8 mA	STD	0.63	9.64	0.05	1.40	0.45	9.82	9.62	2.11	2.12	12.23	12.04	ns
	-1	0.53	8.20	0.04	1.19	0.38	8.35	8.18	2.11	2.12	10.41	10.24	ns
12 mA	STD	0.63	9.64	0.05	1.40	0.45	9.82	9.62	2.11	2.12	12.23	12.04	ns
	-1	0.53	8.20	0.04	1.19	0.38	8.35	8.18	2.11	2.12	10.41	10.24	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-74 • 1.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	8.47	0.05	1.54	0.45	7.38	9.05	1.81	1.45	9.80	11.47	ns
	-1	0.53	7.21	0.04	1.31	0.38	6.28	7.70	1.81	1.45	8.34	9.75	ns
4 mA	STD	0.63	5.24	0.05	1.54	0.45	5.25	5.75	2.00	1.78	7.67	8.17	ns
	-1	0.53	4.45	0.04	1.31	0.38	4.46	4.89	2.00	1.78	6.52	6.95	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-75 • 1.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	13.07	0.05	1.40	0.45	13.86	13.83	1.82	1.39	16.28	16.25	ns
	-1	0.53	11.12	0.04	1.19	0.38	11.79	11.76	1.82	1.39	13.85	13.82	ns
4 mA	STD	0.63	10.04	0.05	1.40	0.45	11.03	10.33	2.00	1.71	13.45	12.75	ns
	-1	0.53	8.54	0.04	1.19	0.38	9.38	8.79	2.01	1.72	11.44	10.84	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-80 • 3.3 V PCI/PCI-X

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.628	2.50	0.05	0.92	0.45	1.23	0.91	3.02	3.48	2.40	2.11	ns
–1	0.53	2.12	0.04	0.78	0.38	1.23	0.91	2.57	2.96	2.41	2.11	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-81 • 3.3 V PCI/PCI-X

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.628	2.90	0.05	0.90	0.45	1.23	0.91	3.02	3.48	2.40	2.11	ns
–1	0.53	2.47	0.04	0.77	0.38	1.23	0.91	2.57	2.96	2.41	2.11	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Differential I/O Characteristics

Physical Implementation

Configuration of the I/O modules as a differential pair is handled by Actel Designer software when the user instantiates a differential I/O macro in the design.

Differential I/Os can also be used in conjunction with the embedded Input Register (InReg), Output Register (OutReg), Enable Register (EnReg), and Double Data Rate (DDR). However, there is no support for bidirectional I/Os or tristates with the LVPECL standards.

LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard. It requires that one data bit be carried through two signal lines, so two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in [Figure 2-12 on page 2-50](#). The building blocks of the LVDS transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVPECL implementation because the output standard specifications are different.

Along with LVDS I/O, ProASIC3 also supports Bus LVDS structure and Multipoint LVDS (M-LVDS) configuration (up to 40 nodes).

DDR Module Specifications

Input DDR Module

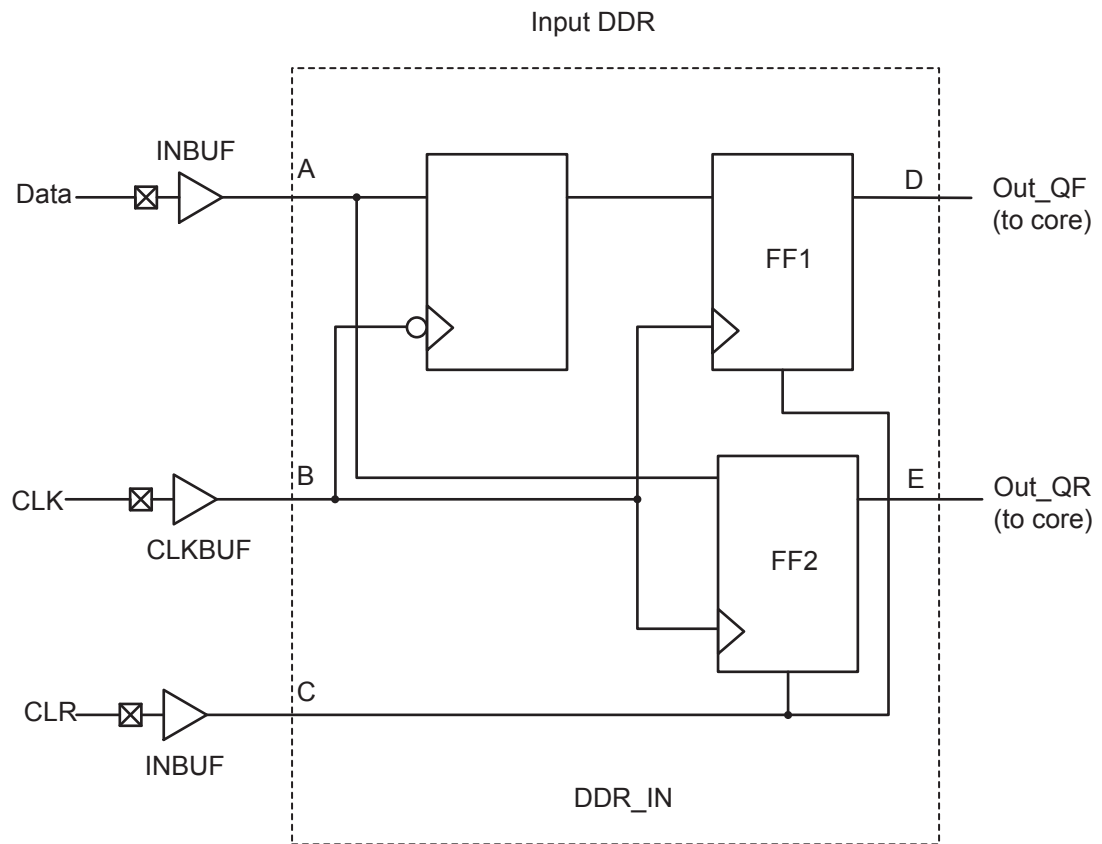


Figure 2-20 • Input DDR Timing Model

Table 2-98 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t_{DDRCLKQ1}	Clock-to-Out Out_QR	B, D
t_{DDRCLKQ2}	Clock-to-Out Out_QF	B, E
t_{DDRISUD}	Data Setup Time of DDR Input	A, B
$t_{\text{DDR IHD}}$	Data Hold Time of DDR Input	A, B
$t_{\text{DDRICLR2Q1}}$	Clear-to-Out Out_QR	C, D
$t_{\text{DDRICLR2Q2}}$	Clear-to-Out Out_QF	C, E
$t_{\text{DDRIREMCLR}}$	Clear Removal	C, B
$t_{\text{DDRIRECCLR}}$	Clear Recovery	C, B

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [Fusion](#), [IGLOO/e](#), and [ProASIC3/E Macro Library Guide](#).

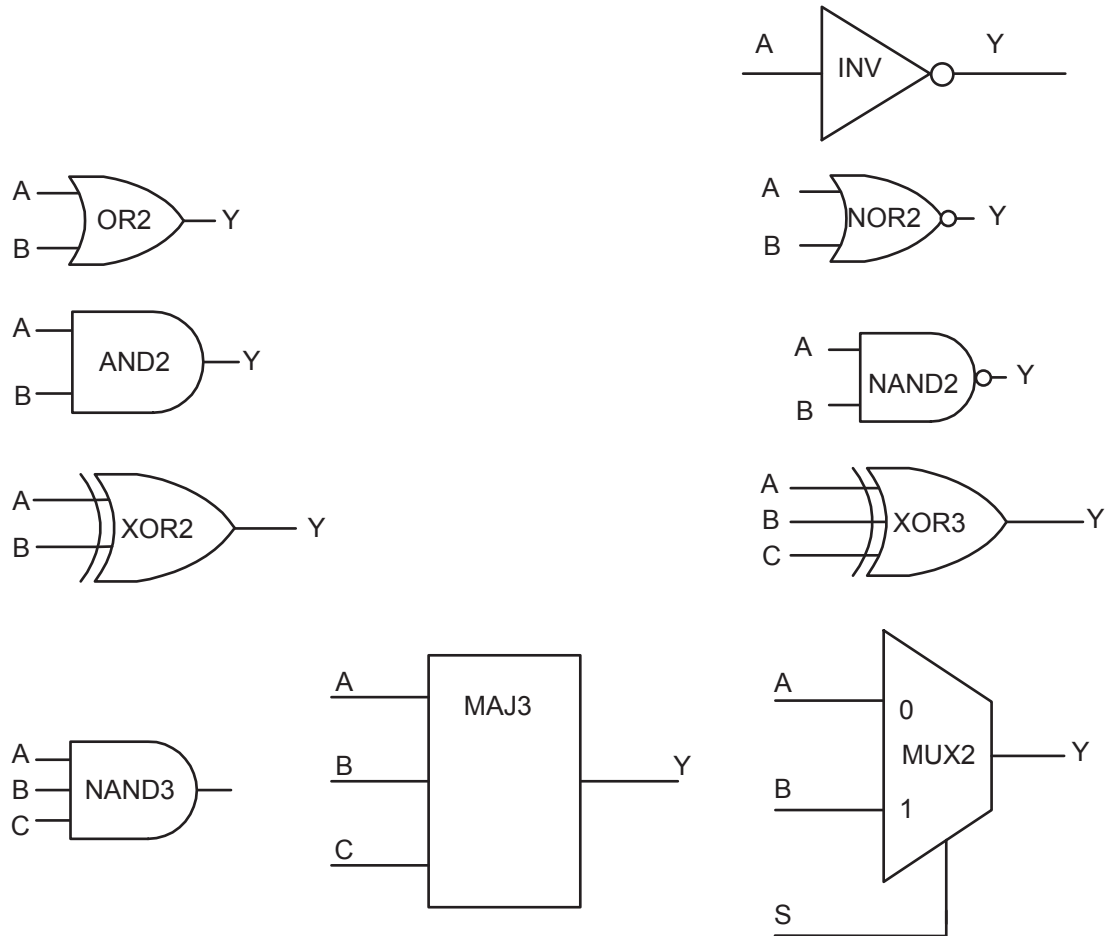


Figure 2-24 • Sample of Combinatorial Cells

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

Table 2-116 • Automotive ProASIC3 CCC/PLL Specification

Parameter	Minimum	Typical	Maximum	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		350	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		160 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Input Period Jitter			1.5	ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Max Peak-to-Peak Period Jitter			
	1 Global Network Used		3 Global Networks Used	
0.75 MHz to 24 MHz	0.50%		0.70%	
24 MHz to 100 MHz	1.00%		1.20%	
100 MHz to 250 MHz	1.75%		2.00%	
250 MHz to 350 MHz	2.50%		5.60%	
Acquisition Time				
(A3P250 and A3P1000 only) LockControl = 0			300	μs
LockControl = 1			300	μs
(all other dies) LockControl = 0			300	μs
LockControl = 1			6.0	ms
Tracking Jitter ⁴				
(A3P250 and A3P1000 only) LockControl = 0			1.6	ns
LockControl = 1			1.6	ns
(all other dies) LockControl = 0			1.6	ns
LockControl = 1			0.8	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 ^{1, 2}	0.6		5.56	ns
Delay Range in Block: Programmable Delay 2 ^{1, 2}	0.025		5.56	ns
Delay Range in Block: Fixed Delay ^{1, 2}		2.2		ns

Notes:

1. This delay is a function of voltage and temperature. See [Table 2-5 on page 2-5](#) for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.5\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.
4. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.

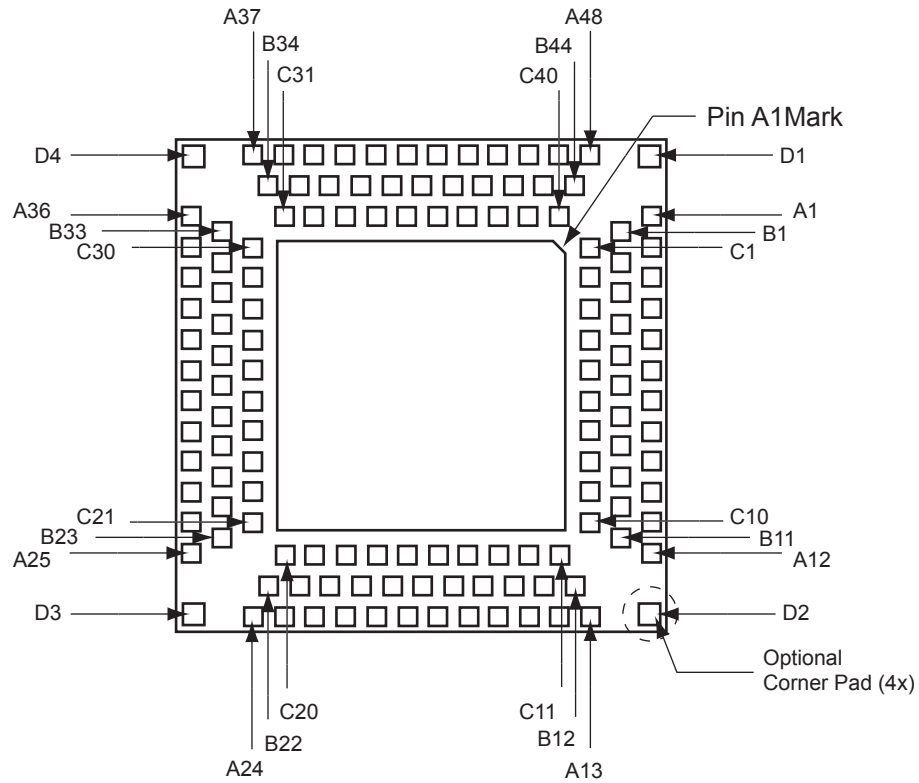
Table 2-119 • RAM4K9
Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{AS}	Address Setup Time	0.30	0.35	ns
t_{AH}	Address Hold Time	0.00	0.00	ns
t_{ENS}	REN, WEN Setup Time	0.17	0.20	ns
t_{ENH}	REN, WEN Hold Time	0.12	0.14	ns
t_{BKS}	BLK Setup Time	0.28	0.33	ns
t_{BKH}	BLK Hold Time	0.02	0.03	ns
t_{DS}	Input data (DIN) Setup Time	0.22	0.26	ns
t_{DH}	Input data (DIN) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on DOUT (output retained, WMODE = 0)	2.13	2.50	ns
	Clock High to New Data Valid on DOUT (flow-through, WMODE = 1)	2.81	3.30	ns
t_{CKQ2}	Clock High to New Data Valid on DOUT (pipelined)	1.07	1.25	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.28	0.33	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.26	0.30	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.38	0.45	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.42	0.49	ns
t_{RSTBQ}	RESET Low to Data Out Low on DOUT (flow-through)	1.10	1.29	ns
	RESET Low to Data Out Low on DOUT (pipelined)	1.10	1.29	ns
$t_{REMRSTB}$	RESET Removal	0.34	0.40	ns
$t_{RECRSTB}$	RESET Recovery	1.79	2.10	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.25	0.30	ns
t_{CYC}	Clock Cycle Time	3.85	4.53	ns
F_{MAX}	Maximum Frequency	260	221	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

QN132



Notes:

1. This is the bottom view of the package.
2. The die attach paddle center of the package is tied to ground (GND).

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.actel.com/products/solutions/package/docs.aspx>.

QN132	
Pin Number	A3P250 Function
A1	GAB2/IO117UPB3
A2	IO117VPB3
A3	VCCIB3
A4	GFC1/IO110PDB3
A5	GFB0/IO109NPB3
A6	VCCPLF
A7	GFA1/IO108PPB3
A8	GFC2/IO105PPB3
A9	IO103NDB3
A10	VCC
A11	GEA1/IO98PPB3
A12	GEA0/IO98NPB3
A13	GEC2/IO95RSB2
A14	IO91RSB2
A15	VCC
A16	IO90RSB2
A17	IO87RSB2
A18	IO85RSB2
A19	IO82RSB2
A20	IO76RSB2
A21	IO70RSB2
A22	VCC
A23	GDB2/IO62RSB2
A24	TDI
A25	TRST
A26	GDC1/IO58UDB1
A27	VCC
A28	IO54NDB1
A29	IO52NDB1
A30	GCA2/IO51PPB1
A31	GCA0/IO50NPB1
A32	GCB1/IO49PDB1
A33	IO47NSB1
A34	VCC
A35	IO41NPB1
A36	GBA2/IO41PPB1

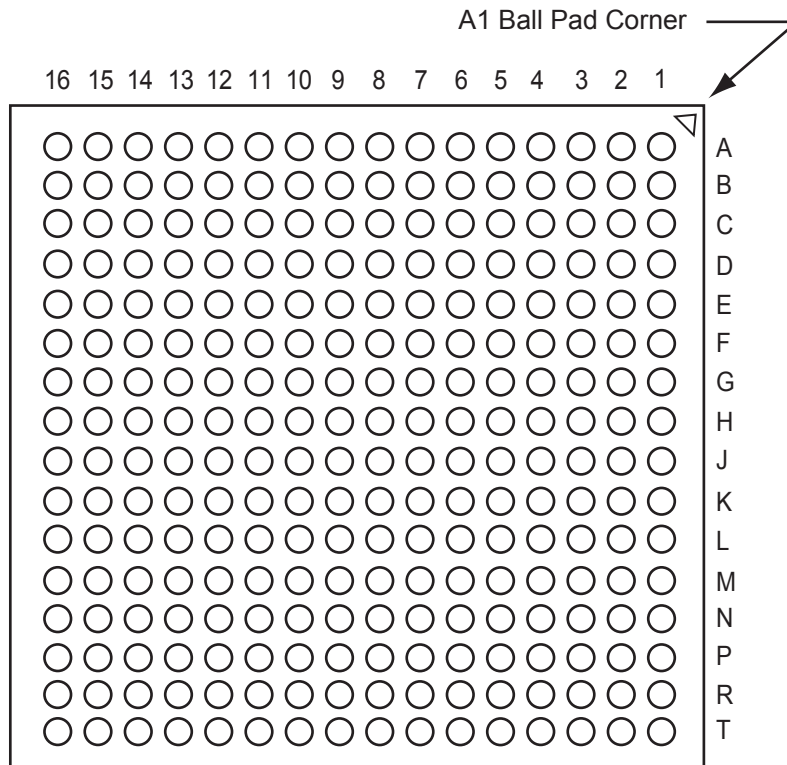
QN132	
Pin Number	A3P250 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO118VDB3
B2	GAC2/IO116UDB3
B3	GND
B4	GFC0/IO110NDB3
B5	VCOMPLF
B6	GND
B7	GFB2/IO106PSB3
B8	IO103PDB3
B9	GND
B10	GEB0/IO99NDB3
B11	VMV3
B12	GEB2/IO96RSB2
B13	IO92RSB2
B14	GND
B15	IO89RSB2
B16	IO86RSB2
B17	GND
B18	IO78RSB2
B19	IO72RSB2
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO58VDB1

QN132	
Pin Number	A3P250 Function
B25	GND
B26	IO54PDB1
B27	GCB2/IO52PDB1
B28	GND
B29	GCB0/IO49NDB1
B30	GCC1/IO48PDB1
B31	GND
B32	GBB2/IO42PDB1
B33	VMV1
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO118UDB3
C2	IO116VDB3
C3	VCC
C4	GFB1/IO109PPB3
C5	GFA0/IO108NPB3
C6	GFA2/IO107PSB3
C7	IO105NPB3
C8	VCCIB3
C9	GEB1/IO99PDB3
C10	GNDQ
C11	GEA2/IO97RSB2
C12	IO94RSB2
C13	VCCIB2
C14	IO88RSB2
C15	IO84RSB2
C16	IO80RSB2

FG144		FG144		FG144	
Pin Number	A3P125 Function	Pin Number	A3P125 Function	Pin Number	A3P125 Function
A1	GNDQ	D1	IO128RSB1	G1	GFA1/IO121RSB1
A2	VMV0	D2	IO129RSB1	G2	GND
A3	GAB0/IO02RSB0	D3	IO130RSB1	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO67RSB1	G4	GFA0/IO122RSB1
A5	IO11RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO18RSB0	D7	GBC0/IO35RSB0	G7	GND
A8	VCC	D8	GBC1/IO36RSB0	G8	GDC1/IO61RSB0
A9	IO25RSB0	D9	GBB2/IO43RSB0	G9	IO48RSB0
A10	GBA0/IO39RSB0	D10	IO28RSB0	G10	GCC2/IO59RSB0
A11	GBA1/IO40RSB0	D11	IO44RSB0	G11	IO47RSB0
A12	GNDQ	D12	GCB1/IO53RSB0	G12	GCB2/IO58RSB0
B1	GAB2/IO69RSB1	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO125RSB1	H2	GFB2/IO119RSB1
B3	GAA0/IO00RSB0	E3	GFC1/IO126RSB1	H3	GFC2/IO118RSB1
B4	GAA1/IO01RSB0	E4	VCCIB1	H4	GEC1/IO112RSB1
B5	IO08RSB0	E5	IO68RSB1	H5	VCC
B6	IO14RSB0	E6	VCCIB0	H6	IO50RSB0
B7	IO19RSB0	E7	VCCIB0	H7	IO60RSB0
B8	IO22RSB0	E8	GCC1/IO51RSB0	H8	GDB2/IO71RSB1
B9	GBB0/IO37RSB0	E9	VCCIB0	H9	GDC0/IO62RSB0
B10	GBB1/IO38RSB0	E10	VCC	H10	VCCIB0
B11	GND	E11	GCA0/IO56RSB0	H11	IO49RSB0
B12	VMV0	E12	IO46RSB0	H12	VCC
C1	IO132RSB1	F1	GFB0/IO123RSB1	J1	GEB1/IO110RSB1
C2	GFA2/IO120RSB1	F2	VCOMPLF	J2	IO115RSB1
C3	GAC2/IO131RSB1	F3	GFB1/IO124RSB1	J3	VCCIB1
C4	VCC	F4	IO127RSB1	J4	GEC0/IO111RSB1
C5	IO10RSB0	F5	GND	J5	IO116RSB1
C6	IO12RSB0	F6	GND	J6	IO117RSB1
C7	IO21RSB0	F7	GND	J7	VCC
C8	IO24RSB0	F8	GCC0/IO52RSB0	J8	TCK
C9	IO27RSB0	F9	GCB0/IO54RSB0	J9	GDA2/IO70RSB1
C10	GBA2/IO41RSB0	F10	GND	J10	TDO
C11	IO42RSB0	F11	GCA1/IO55RSB0	J11	GDA1/IO65RSB0
C12	GBC2/IO45RSB0	F12	GCA2/IO57RSB0	J12	GDB1/IO63RSB0

FG144		FG144		FG144	
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
A1	GNDQ	D1	IO112NDB3	G1	GFA1/IO108PPB3
A2	VMV0	D2	IO112PDB3	G2	GND
A3	GAB0/IO02RSB0	D3	IO116VDB3	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO118UPB3	G4	GFA0/IO108NPB3
A5	IO16RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO29RSB0	D7	GBC0/IO35RSB0	G7	GND
A8	VCC	D8	GBC1/IO36RSB0	G8	GDC1/IO58UPB1
A9	IO33RSB0	D9	GBB2/IO42PDB1	G9	IO53NDB1
A10	GBA0/IO39RSB0	D10	IO42NDB1	G10	GCC2/IO53PDB1
A11	GBA1/IO40RSB0	D11	IO43NPB1	G11	IO52NDB1
A12	GNDQ	D12	GCB1/IO49PPB1	G12	GCB2/IO52PDB1
B1	GAB2/IO117UDB3	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO110NDB3	H2	GFB2/IO106PDB3
B3	GAA0/IO00RSB0	E3	GFC1/IO110PDB3	H3	GFC2/IO105PSB3
B4	GAA1/IO01RSB0	E4	VCCIB3	H4	GEC1/IO100PDB3
B5	IO14RSB0	E5	IO118VPB3	H5	VCC
B6	IO19RSB0	E6	VCCIB0	H6	IO79RSB2
B7	IO22RSB0	E7	VCCIB0	H7	IO65RSB2
B8	IO30RSB0	E8	GCC1/IO48PDB1	H8	GDB2/IO62RSB2
B9	GBB0/IO37RSB0	E9	VCCIB1	H9	GDC0/IO58VPB1
B10	GBB1/IO38RSB0	E10	VCC	H10	VCCIB1
B11	GND	E11	GCA0/IO50NDB1	H11	IO54PSB1
B12	VMV1	E12	IO51NDB1	H12	VCC
C1	IO117VDB3	F1	GFB0/IO109NPB3	J1	GEB1/IO99PDB3
C2	GFA2/IO107PPB3	F2	VCOMPLF	J2	IO106NDB3
C3	GAC2/IO116UDB3	F3	GFB1/IO109PPB3	J3	VCCIB3
C4	VCC	F4	IO107NPB3	J4	GEC0/IO100NDB3
C5	IO12RSB0	F5	GND	J5	IO88RSB2
C6	IO17RSB0	F6	GND	J6	IO81RSB2
C7	IO24RSB0	F7	GND	J7	VCC
C8	IO31RSB0	F8	GCC0/IO48NDB1	J8	TCK
C9	IO34RSB0	F9	GCB0/IO49NPB1	J9	GDA2/IO61RSB2
C10	GBA2/IO41PDB1	F10	GND	J10	TDO
C11	IO41NDB1	F11	GCA1/IO50PDB1	J11	GDA1/IO60UDB1
C12	GBC2/IO43PPB1	F12	GCA2/IO51PDB1	J12	GDB1/IO59UDB1

FG256



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.actel.com/products/solutions/package/docs.aspx>.

FG256		FG256		FG256	
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
G13	GCC1/IO48PPB1	K1	GFC2/IO105PDB3	M5	VMV3
G14	IO47NPB1	K2	IO107NPB3	M6	VCCIB2
G15	IO54PDB1	K3	IO104PPB3	M7	VCCIB2
G16	IO54NDB1	K4	NC	M8	NC
H1	GFB0/IO109NPB3	K5	VCCIB3	M9	IO74RSB2
H2	GFA0/IO108NDB3	K6	VCC	M10	VCCIB2
H3	GFB1/IO109PPB3	K7	GND	M11	VCCIB2
H4	VCOMPLF	K8	GND	M12	VMV2
H5	GFC0/IO110NPB3	K9	GND	M13	NC
H6	VCC	K10	GND	M14	GDB1/IO59UPB1
H7	GND	K11	VCC	M15	GDC1/IO58UDB1
H8	GND	K12	VCCIB1	M16	IO56NDB1
H9	GND	K13	IO52NPB1	N1	IO103NDB3
H10	GND	K14	IO55RSB1	N2	IO101PPB3
H11	VCC	K15	IO53NPB1	N3	GEC1/IO100PPB3
H12	GCC0/IO48NPB1	K16	IO51NDB1	N4	NC
H13	GCB1/IO49PPB1	L1	IO105NDB3	N5	GNDQ
H14	GCA0/IO50NPB1	L2	IO104NPB3	N6	GEA2/IO97RSB2
H15	NC	L3	NC	N7	IO86RSB2
H16	GCB0/IO49NPB1	L4	IO102RSB3	N8	IO82RSB2
J1	GFA2/IO107PPB3	L5	VCCIB3	N9	IO75RSB2
J2	GFA1/IO108PDB3	L6	GND	N10	IO69RSB2
J3	VCCPLF	L7	VCC	N11	IO64RSB2
J4	IO106NDB3	L8	VCC	N12	GNDQ
J5	GFB2/IO106PDB3	L9	VCC	N13	NC
J6	VCC	L10	VCC	N14	VJTAG
J7	GND	L11	GND	N15	GDC0/IO58VDB1
J8	GND	L12	VCCIB1	N16	GDA1/IO60UDB1
J9	GND	L13	GDB0/IO59VPB1	P1	GEB1/IO99PDB3
J10	GND	L14	IO57VDB1	P2	GEB0/IO99NDB3
J11	VCC	L15	IO57UDB1	P3	NC
J12	GCB2/IO52PPB1	L16	IO56PDB1	P4	NC
J13	GCA1/IO50PPB1	M1	IO103PDB3	P5	IO92RSB2
J14	GCC2/IO53PPB1	M2	NC	P6	IO89RSB2
J15	NC	M3	IO101NPB3	P7	IO85RSB2
J16	GCA2/IO51PDB1	M4	GEC0/IO100NPB3	P8	IO81RSB2